

ABSTRACT OF THE DISCLOSURE

To fabricate a buried ribbon laser, a thin n-doped layer is formed on a p-doped layer immediately adjacent an active layer. After etching the active layer to form the ribbon, the ribbon is buried in an n-doped layer so that the four lateral faces of the ribbon are all in contact with an n-doped layer. One face is in contact with the thin layer and the other three faces are in contact with the burying layer. This improves the electrical confinement of the ribbon.

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